Taipei, Taiwan
2027 IEEE ISPSD June 13-17 TICC, Taipei, Taiwan

2027 IEEE International Symposium on Power Semiconductor Devices and ICs

PAPER SUBMISSION OPENS SOON!

Why You Should Present at ISPSD 2027

ISPSD is the premier forum for power semiconductor devices and ICs. In vibrant Taipei, share your breakthrough research and connect with leading experts from around the world.
Visit our website to learn more: ispsd2027.com

Important Dates

Time is running out to finalize your submission! Please take note of the key deadlines:

- **November 11, 2026 (UTC−0600):** Paper submission site open & Visa information release
- **December 16, 2026 (23:59, UTC−0600):** 4-page full paper submission deadline
- **February 2, 2027 (UTC−0600):** Author notification & Registration for the symposium
- **February 19, 2027 (23:59, UTC−0600):** Final submission deadline for final paper and copyright filing

Important Notes

- **Submission Policy:** ISPSD 2027 has revised its submission process. Authors are required to submit a 4-page full paper upon initial submission. Traditional "Abstract Submissions" will NOT be accepted, and there will be NO late news session. Please prepare your full draft early to avoid last-minute delays!
- **PRC Passport Holders:** Authors holding a PRC passport and traveling directly from Mainland China to present onsite are strongly advised to start their Exit & Entry Permit (入台證) application **BEFORE** December 16, 2026.

Submission Tracks

- **High Voltage Devices (HV):** High voltage silicon based discrete devices (>200V) such as SJ-MOSFETs, IGBTs, thyristors and pn-diodes
- **Low Voltage Devices and Power IC Device Technology (LVT):** Low voltage silicon based discrete power devices (≤200V) and devices for power ICs of all voltage ranges
- **Power IC Design (ICD):** Circuit design and demonstration using power IC technology platform
- **GaN and Compound Materials (GaN):** GaN and nitride-based compound materials (e.g., AlN) based power devices, technology and integration, materials, and processing
- **SiC and Other Materials (SiC):** SiC and other materials (e.g., Ga_2O_3, diamond) based power devices, technology and integration, materials, and processing
- **Module and Packaging Technologies (PK):** System integration in package module and package technology for discrete power devices and power ICs

Guidelines & Formatting

- **Paper Template:** Download from the IEEE Manuscript Templates for Conference Proceedings
- **Page Limit:** 4 pages
- **Page Size:** US Letter
- **File Format:** Adobe PDF (.pdf)

Contact Information

For questions regarding paper submission or the technical program, please reach out to the chairs:

- **General Chair:**
  Dr. Tom Tsai
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